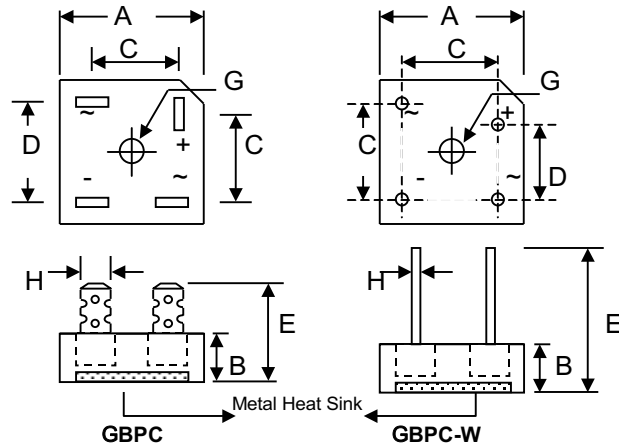


Features

- Glass Passivated Die Construction
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- Electrically Isolated Epoxy Case for Maximum Heat Dissipation
- Case to Terminal Isolation Voltage 2500V
- UL Recognized File # E223064
- Green Products in Compliance with the RoHS Directive



Mechanical Data

- Case: Epoxy Case with Heat Sink Internally Mounted in the Bridge Encapsulation
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Symbols Marked on Case
- Mounting: Through Hole for #8 Screw
- Weight: GBPC 24 grams (approx.)
GBPC-W 21 grams (approx.)
- Marking: Type Number

"W" Suffix Designates Wire Leads
No Suffix Designates Faston Terminals

*All Models are Available on B(Height)=7.62mm Max. Epoxy Case

Dim	GBPC		GBPC-W	
	Min	Max	Min	Max
A	28.40	28.70	28.40	28.70
B	10.97	11.23	10.97	11.23
C	15.70	16.70	17.10	19.10
D	17.50	18.50	10.90	11.90
E	22.86	25.40	30.50	—
G	Hole for #8 screw, 4.90Ø Nominal			
H	6.35 Typical		0.97Ø	1.07Ø
All Dimension in mm				

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

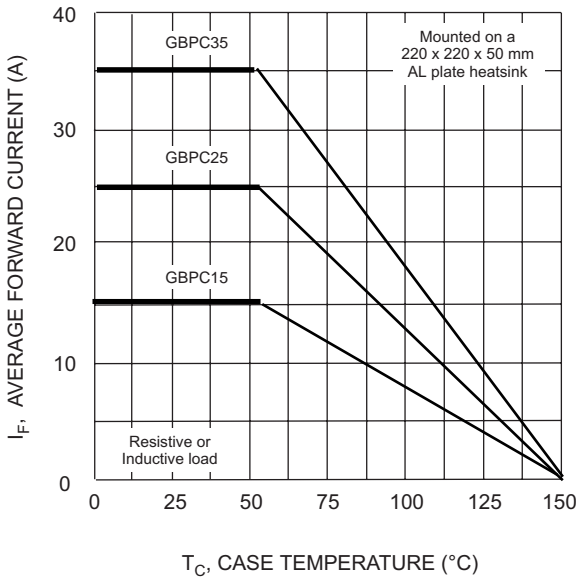
Characteristics	Symbol	-00/W-G	-01/W-G	-02/W-G	-04/W-G	-06/W-G	-08/W-G	-10/W-G	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Working Peak Reverse Voltage	V _{RWM}								
DC Blocking Voltage	V _R								
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectifier Output Current @T _C = 55°C	I _O				15	25	35		A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave Superimposed on rated load (JEDEC Method)	I _{FSM}				300	300	400		A
Forward Voltage Drop (per element)	V _{FM}				1.1				V
Peak Reverse Current At Rated DC Blocking Voltage	I _{RM}				5.0	500			µA
I ² t Rating for Fusing (t < 8.3ms) (Note 1)	I ² t				375	375	660		A ² s

Maximum Ratings and Elect

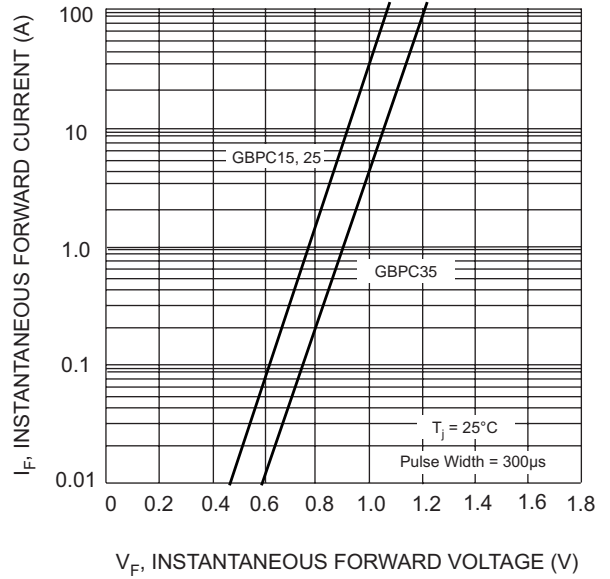
acteristics @T_A=25°C unless otherwise specified

Typical Junction Capacitance (per element) (Note 2)	C _j	300	pF
Typical Thermal Resistance Junction to Case (per element) (Note 3)	R _{θJC}	5.3 3.6 3.0	K/W
RMS Isolation Voltage from Case to Lead	V _{ISO}	2500	V
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

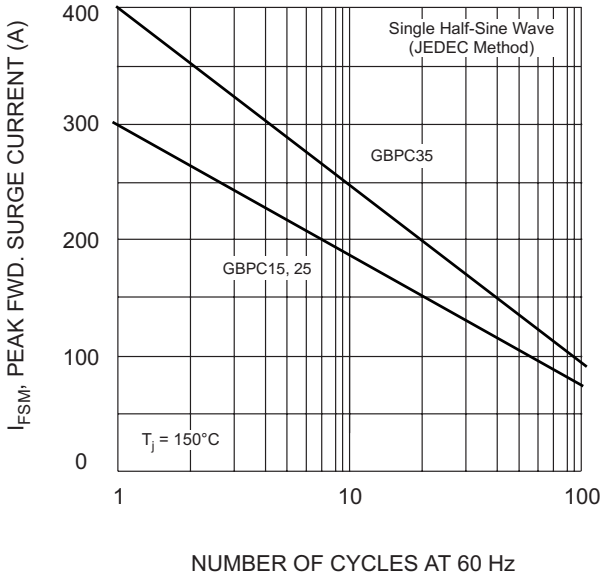
- Note: 1. Measured at non-repetitive, for t > 1ms and < 8.3ms.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
3. Thermal resistance junction to case mounted on heatsink.



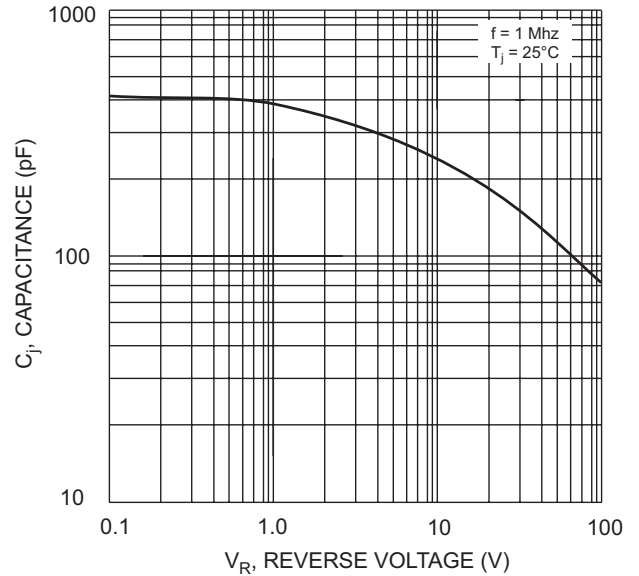
T_C , CASE TEMPERATURE ($^{\circ}C$)
Fig. 1 Forward Current Derating Curve



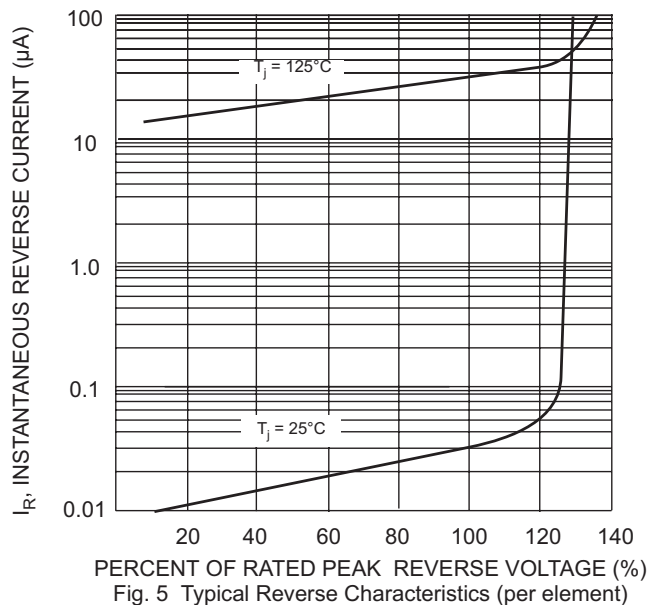
V_F , INSTANTANEOUS FORWARD VOLTAGE (V)
Fig. 2 Typical Forward Characteristics (per element)



NUMBER OF CYCLES AT 60 Hz
Fig. 3 Max Non-Repetitive Surge Current



V_R , REVERSE VOLTAGE (V)
Fig. 4 Typical Junction Capacitance (per element)



PERCENT OF RATED PEAK REVERSE VOLTAGE (%)
Fig. 5 Typical Reverse Characteristics (per element)

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